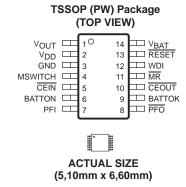
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features

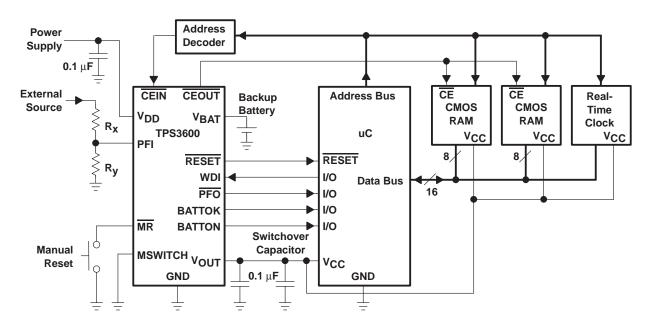
- Supply Current of 40 μA (Max)
- Precision Supply Voltage Monitor
 - 2.0 V, 2.5 V, 3.3 V, 5.0 V
 - Other Versions on Request
- Watchdog Timer With 800-ms Time-Out
- Backup-Battery Voltage Can Exceed V_{DD}
- Power-On Reset Generator With Fixed 100-ms Reset Delay Time
- Battery OK Output
- Voltage Monitor for Power-Fail or Low-Battery Monitoring
- Manual Switchover to Battery-Backup Mode
- Chip-Enable Gating -3 ns (at V_{DD} = 5 V)
 Max. Propagation Delay
- Manual Reset
- Battery Freshness Seal
- 14-Pin TSSOP Package
- Temperature Range . . . −40°C to 85°C

typical applications

- Fax Machines
- Set-Top Boxes
- Advanced Voice Mail Systems
- Portable Battery Powered Equipment
- Computer Equipment
- Advanced Modems
- Automotive Systems
- Portable Long-Time Monitoring Equipment
- Point of Sale Equipment



typical operating circuit





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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description

The TPS3600 family of supervisory circuits monitor and control processor activity. In case of power-fail or brownout conditions, the backup-battery switchover function of TPS3600 allows to run a low-power processor and its peripherals from the installed backup battery without asserting a reset beforehand.

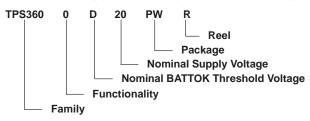
During power on, $\overline{\text{RESET}}$ is asserted when the supply voltage $(V_{DD} \text{ or } V_{BAT})$ becomes higher than V_{res} . Thereafter, the supply voltage supervisor monitors V_{OUT} and keeps $\overline{\text{RESET}}$ output active as long as V_{OUT} remains below the threshold voltage (V_{IT}) . An internal timer delays the return of the output to the inactive state (high) to ensure proper system reset. This delay timer starts its time-out, after V_{OUT} has risen above the threshold voltage (V_{IT}) . In case of a brownout or power failure of both supply sources, a voltage drop below the threshold voltage (V_{IT}) get detected and the output becomes active (low) again.

The product spectrum is designed for supply voltages of 2 V, 2.5 V, 3.3 V, and 5 V. The circuits are available in a 14-pin TSSOP package. They are characterized for operation over a temperature range of –40°C to 85°C.

PACKAGE INFORMATION

T _A	DEVICE NAME		
–40°C to 85°C	TPS3600D20		
	TPS3600D25		
	TPS3600D33		
	TPS3600D50		

ordering information application specific versions (see Note)



DEVICE NAME	NOMINAL VOLTAGE, V _{NOM}
TPS3600x20 PW	2.0 V
TPS3600x25 PW	2.5 V
TPS3600x33 PW	3.3 V
TPS3600x50 PW	5.0 V

	NOMINAL BATTOK
DEVICE NAME	THRESHOLD VOLTAGE, VBOK
TPS3600Dxx PW	V _{IT} + 7%
TPS3600Fxx PW [†]	V _{IT} + 6%
TPS3600Hxx PW [†]	V _{IT} + 8%
TPS3600Jxx PW [†]	V _{IT} + 10%

[†] For the application specific versions, please contact the local TI sales office for availability and lead time.



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FUNCTION TABLES

V _{DD} > V _{SW}	V _{OUT} > V _{IT}	V _{DD} > V _{BAT}	MSWITCH	MR	Vout	BATTON	RESET	CEOUT
0	0	0	0	0	V _{BAT}	1	0	DIS
0	0	0	0	1	VBAT	1	0	DIS
0	0	0	1	0	VBAT	1	0	DIS
0	0	0	1	1	V_{BAT}	1	0	DIS
0	0	1	0	0	V_{DD}	0	0	DIS
0	0	1	0	1	V_{DD}	0	0	DIS
0	0	1	1	0	VBAT	1	0	DIS
0	0	1	1	1	VBAT	1	0	DIS
0	1	0	0	0	VBAT	1	0	DIS
0	1	0	0	1	V_{BAT}	1	1	EN
0	1	0	1	0	V_{BAT}	1	0	DIS
0	1	0	1	1	VBAT	1	1	EN
0	1	1	0	0	V_{DD}	0	0	DIS
0	1	1	0	1	V_{DD}	0	1	EN
0	1	1	1	0	VBAT	1	0	DIS
0	1	1	1	1	VBAT	1	1	EN
1	1	0	0	0	V_{DD}	0	0	DIS
1	1	0	0	1	V_{DD}	0	1	EN
1	1	0	1	0	VBAT	1	0	DIS
1	1	0	1	1	V _{BAT}	1	1	EN
1	1	1	0	0	V_{DD}	0	0	DIS
1	1	1	0	1	V_{DD}	0	1	EN
1	1	1	1	0	V_{BAT}	1	0	DIS
1	1	1	1	1	V_{BAT}	1	1	EN

V _{BAT} > V _{BOK}	BATTOK
0	0
1	1

CONDITION: V_{OUT} > V_{DD(min)}

CEIN	CEOUT
0	0
1	1

CONDITION: Enabled

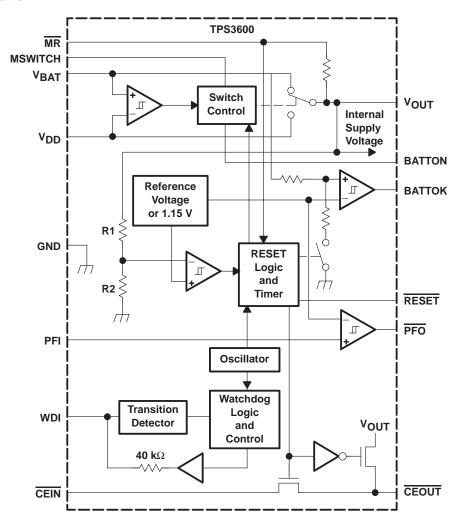
PFI > V _{PFI}	PFO
0	0
1	1

CONDITION: V_{OUT} > V_{DD(min)}

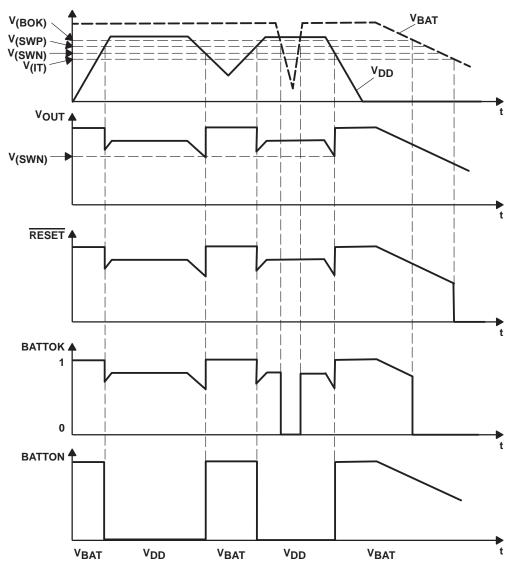


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functional schematic



timing diagram



NOTES: A. MSWITCH = 0, $\overline{MR} = 1$

NOTES: B. Timing diagram shown under normal operation, not in freshness seal mode.

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Terminal Functions

TERMINAL		1/0	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
BATTOK	9	0	Battery status output	
BATTON	6	0	Logic output/external bypass switch driver output	
CEIN	5	I	Chip-enable input	
CEOUT	10	0	Chip-enable output	
GND	3	I	Ground	
MR	11	I	Manual reset input	
MSWITCH	4	I	Manual switch to force device into battery-backup mode (connect to GND if not used)	
PFI	7	I	Power-fail comparator input (connect to GND if not used)	
PFO	8	0	Power-fail comparator output	
RESET	13	0	Active-low reset output	
VBAT	14	I	Backup-battery input	
V_{DD}	2	I	Input supply voltage	
VOUT	1	0	Supply output	
WDI	12	I	Watchdog timer input	

detailed description

battery freshness seal

The battery freshness seal of the TPS3600 family disconnects the backup battery from the internal circuitry until it is needed. This ensures that the backup battery connected to V_{BAT} should be fresh when the final product is put to use. The following steps explain how to enable the freshness seal mode:

- 1. Connect V_{BAT} (V_{BAT} > V_{BAT(min)})
- 2. Ground PFO
- 3. Connect PFI to V_{DD} or PFI > $V_{(PFI)}$
- Connect V_{DD} to power supply (V_{DD} > V_{IT})
- 5. Ground \overline{MR}
- 6. Power down V_{DD}
- 7. The freshness seal mode is entered and pins \overline{PFO} and \overline{MR} can be disconnected.

The battery freshness seal mode is disabled by the positive-going edge of RESET when V_{DD} is applied.

BATTOK output

This is a logic feedback of the device to indicate the status of the backup battery. The supervisor checks the battery voltage every 200 ms with a voltage divider load of approximately 100 K Ω and a measure cycle on-time of 25 μ s. This measurement cycle starts after the reset is released. If the battery voltage V_{BAT} is below the negative-going threshold voltage V_(BOK), the indicator BATTOK does a high-to-low transition. Otherwise, its status remains to the V_{OUT} level.

Table 1. Typical Values for BATTOK Indication

SUPERVISOR TYPE	V _{IT} TYP	V _{BOK} MIN	V _{BOK} TYP	V _{BOK} MAX
TPS3600D20	1.78 V	1.84 V	1.91 V	1.97 V
TPS3600D25	2.22 V	2.3 V	2.38 V	2.46 V
TPS3600D33	2.93 V	3.04 V	3.14 V	3.24 V
TPS3600D50	4.40 V	4.56 V	4.71 V	4.86 V



detailed description (continued)

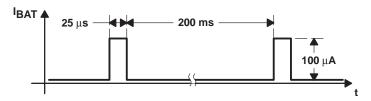


Figure 1. BATTOK Timing

chip-enable signal gating

The internal gating of chip-enable signals (CE) prevents erroneous data from corrupting CMOS RAM during an under-voltage condition. The TPS3600 use a series transmission gate from CEIN to CEOUT. During normal operation (reset not asserted), the CE transmission gate is enabled and passes all CE transitions. When reset is asserted, this path becomes disabled, preventing erroneous data from corrupting the CMOS RAM. The short CE propagation delay from CEIN to CEOUT enables the TPS3600 devices to be used with most processors.

The CE transmission gate is disabled and $\overline{\text{CEIN}}$ is high impedance (disable mode) while reset is asserted. During a power-down sequence when V_{DD} crosses the reset threshold, the CE transmission gate will be disabled and $\overline{\text{CEIN}}$ immediately becomes high impedance if the voltage at $\overline{\text{CEIN}}$ is high. If $\overline{\text{CEIN}}$ is low during reset is asserted, the CE transmission gate will be disabled same time when $\overline{\text{CEIN}}$ goes high, or 15 μ s after reset asserts, whichever occurs first. This will allow the current write cycle to complete during power down. When the CE transmission gate is enabled, the impedance of $\overline{\text{CEIN}}$ appears as a resistor in series with the load at $\overline{\text{CEOUT}}$. The overall device propagation delay through the CE transmission gate depends on V_{OUT} , the source impedance of the device connected to $\overline{\text{CEIN}}$ and the load at $\overline{\text{CEOUT}}$. To achieve minimum propagation delay, the capacitive load at $\overline{\text{CEOUT}}$ should be minimized, and a low-output-impedance driver be used.

During disable mode, the transmission gate is off and an active pullup connects $\overline{\text{CEOUT}}$ to V_{OUT} . This pullup turns off when the transmission gate is enabled.

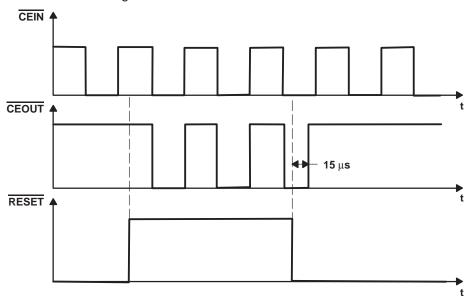


Figure 2. Chip-Enable Timing



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detailed description (continued)

power-fail comparator (PFI and PFO)

An additional comparator is provided to monitor voltages other than the nominal supply voltage. The power-fail input (PFI) will be compared with an internal voltage reference of 1.15 V. If the input voltage falls below the power-fail threshold, $V_{(PFI)}$, of 1.15 V typical, the power-fail output (PFO) goes low. If it goes above $V_{(PFI)}$ plus about 12-mV hysteresis, the output returns to high. By connecting two external resistors, it is possible to supervise any voltages above $V_{(PFI)}$. The sum of both resistors should be about 1 M Ω , to minimize power consumption and also to ensure that the current in the PFI pin can be neglected compared with the current through the resistor network. The tolerance of the external resistors should be not more than 1% to ensure minimal variation of sensed voltage.

If the power-fail comparator is unused, connect PFI to ground and leave PFO unconnected.

BATTON

Most often BATTON is used as a gate drive for an external pass transistor for high-current applications. In addition it can be also used as a logic output to indicate the battery switchover status. BATTON is high when V_{OUT} is connected to V_{BAT} .

BATTON can be directly connected to the gate of a PMOS transistor (see Figure 3). No current-limiting resistor is required. When using a PMOS transistor, it must be connected backwards from the traditional method (see Figure 3). This method orients the body diode from V_{DD} to V_{OUT} and prevents the backup battery from discharging through the FET when its gate is high.

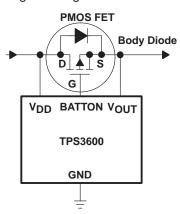


Figure 3. Driving an External MOSFET Transistor With BATTON

backup-battery switchover

In the event of a brownout or power failure, it may be necessary to keep a processor running. If a backup battery is installed at V_{BAT} , the devices automatically connect the processor to backup power when V_{DD} fails. In order to allow the backup battery (e.g., a 3.6-V lithium cell) to have a higher voltage than V_{DD} , this family of supervisors will not connect V_{BAT} to V_{OUT} when V_{BAT} is greater than V_{DD} . V_{BAT} only connects to V_{OUT} (through a 2- Ω switch) when V_{OUT} falls below $V_{(SWN)}$ and V_{BAT} is greater than V_{DD} . When V_{DD} recovers, switchover is deferred either until V_{DD} crosses V_{BAT} , or when V_{DD} rises above the threshold $V_{(SWP)}$. (See the timing diagram)

V _{DD} > V _{BAT}	V _{DD} > V _(SW)	Vout
1	1	V_{DD}
1	0	V_{DD}
0	1	V_{DD}
0	0	Vrat



detailed description (continued)

manual switchover (MSWITCH)

While operating in the normal mode from V_{DD} , the device can be manually forced to operate in the battery-backup mode by connecting MSWITCH to V_{DD} . The table below shows the different switchover modes.

	MSWITCH	STATUS	
V mada	GND	V _{DD} mode	
V _{DD} mode	V_{DD}	Switch to battery-backup mode	
Pottony bookup mode	GND	Battery-backup mode	
Battery-backup mode	V_{DD}	Battery-backup mode	

If the manual switchover feature is not used, MSWITCH must be connected to ground.

watchdog

In a microprocessor- or DSP-based system, it is not only important to supervise the supply voltage, it is also important to ensure the correct program execution. The task of a watchdog is to ensure that the program is not stalled in an indefinite loop. The microprocessor, microcontroller, or the DSP have to toggle the watchdog input within typically 0.8 s to avoid a time-out from occurring. Either a low-to-high or a high-to-low transition resets the internal watchdog timer. If the input is unconnected the watchdog is disabled and will be retriggered internally.

saving current while using the watchdog

The watchdog input is internally driven low during the first 7/8 of the watchdog time-out period, then momentarily pulses high, resetting the watchdog counter. For minimum watchdog input current (minimum overall power consumption), leave WDI low for the majority of the watchdog time-out period, pulsing it low-high-low once within 7/8 of the watchdog time-out period to reset the watchdog timer. If instead, WDI is externally driven high for the majority of the time-out period, a current of e.g. 5 V/40 $k\Omega \approx 125 \,\mu\text{A}$ can flow into WDI.

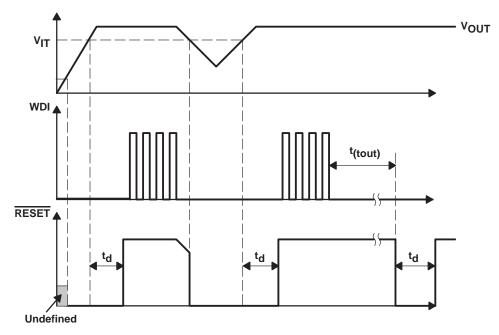


Figure 4. Watchdog Timing



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absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage:	V _{DD} (see Note1)	7 V
	MR and WDI	
	All other pins (see Note 1)	–0.3 V to 7 V
Continuous outp	ut current at V _{OUT} : I _O	
	All other pins, IO	±10 mA
Continuous total	power dissipation	See Dissipation Rating Table
Operating free-a	ir temperature range, TA	–40°C to 85°C
Storage tempera	ature range, T _{sta}	–65°C to 150°C
Lead temperatur	re soldering 1,6 mm (1/16 inch) from case for 10 seconds	260°C

DISSIPATION RATING TABLE

PACKAGE	T _A < 25°C	DERATING FACTOR	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C	POWER RATING	POWER RATING
PW	700 mW	5.6 mW/°C	448 mW	364 mW

recommended operating conditions at specified temperature range

	MIN	MAX	UNIT
Supply voltage, V _{DD}	1.65	5.5	V
Battery supply voltage, VBAT	1.5	5.5	V
Input voltage, V _I	0	V _{OUT} + 0.3	V
High-level input voltage, V _{IH}	0.7 x V _{OUT}		V
Low-level input voltage, all other pins, $V_{\mbox{\scriptsize IL}}$		0.3 x V _{OUT}	V
Continuous output current at V _{OUT} , I _O		200	mA
Input transition rise and fall rate at WDI, MSWITCH, $\Delta t/\Delta V$		100	ns/V
Slew rate at V _{DD} or V _{BAT}		34	mV/μs
Operating free-air temperature range, T _A	-40	85	°C



[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND. For reliable operation the device must not be operated at 7 V for more than t = 1000h continuously.

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electrical characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	_	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
		RESET,	$V_{OUT} = 2.0 \text{ V}, I_{OH} = -400 \mu\text{A}$	V _{OUT} – 0.2 V				
		BATTOK,	$V_{OUT} = 3.3 \text{ V}, I_{OH} = -2 \text{ mA}$	V _{OUT} – 0.4 V				
		BATTON	$V_{OUT} = 5.0 \text{ V}, I_{OH} = -3 \text{ mA}$	VOUT = 0.4 V				
			$V_{OUT} = 1.8 \text{ V}, I_{OH} = -20 \mu\text{A}$	V _{OUT} – 0.3 V				
	High-level output	PFO	$V_{OUT} = 3.3 \text{ V}, I_{OH} = -80 \mu\text{A}$	V _{OUT} – 0.4 V				
Vон	VOH voltage		$V_{OUT} = 5.0 \text{ V}, I_{OH} = -120 \mu\text{A}$				V	
		CEOUT	$V_{OUT} = 2.0 \text{ V}, I_{OH} = -1 \text{ mA}$	V _{OUT} – 0.2 V				
		Enable mode	$V_{OUT} = 3.3 \text{ V}, I_{OH} = -2 \text{ mA}$	V _{OUT} – 0.3 V				
		CEIN = V _{OUT}	$V_{OUT} = 5.0 \text{ V}, I_{OH} = -5 \text{ mA}$	VOUT = 0.5 V				
		CEOUT Disable mode	$V_{OUT} = 3.3 \text{ V}, I_{OH} = -0.5 \text{ mA}$	V _{OUT} – 0.4 V				
		RESET,	$V_{OUT} = 2.0 \text{ V}, I_{OL} = 400 \mu\text{A}$			0.2		
		PFO,	$V_{OUT} = 3.3 \text{ V}, I_{OL} = 2 \text{ mA}$			0.4		
		BATTOK	$V_{OUT} = 5.0 \text{ V}, I_{OL} = 3 \text{ mA}$			0.4		
	VOL Low-level output BATT		$V_{OUT} = 1.8 \text{ V}, I_{OL} = 500 \mu\text{A}$			0.2		
VOL		BATTON	$V_{OUT} = 3.3 \text{ V}, I_{OL} = 3 \text{ mA}$			0.4	V	
	voltago		$V_{OUT} = 5.0 \text{ V}, I_{OL} = 5 \text{ mA}$			0.4		
		CEOUT	$V_{OUT} = 2.0 \text{ V}, I_{OL} = 1 \text{ mA}$			0.2		
		Enable mode	$V_{OUT} = 3.3 \text{ V}, I_{OL} = 2 \text{ mA}$]		0.3		
		CEIN = 0 V	$V_{OUT} = 5.0 \text{ V}, I_{OL} = 5 \text{ mA}$			0.0		
V _{res}	Power-up reset voltag	e (see Note 2)	V _{BAT} > 1.1 V OR V _{DD} > 1.4 V, I _{OL} = 20 μA			0.4	V	
			$I_O = 5 \text{ mA}, V_{DD} = 1.8 \text{ V}$	V _{DD} – 50 mV				
	Normal mode		$I_O = 75 \text{ mA}, V_{DD} = 3.3 \text{ V}$	V _{DD} – 150 mV				
Vout			$I_O = 150 \text{ mA}, V_{DD} = 5 \text{ V}$	V _{DD} – 250 mV			V	
	Battery-backup mode		$I_{O} = 4 \text{ mA}, \qquad V_{BAT} = 1.5 \text{ V}$	V _{BAT} – 50 mV				
	, '		$I_O = 75 \text{ mA}, V_{BAT} = 3.3 \text{ V}$	V _{BAT} – 150 mV				
r=1=/===\	V _{DD} to V _{OUT} on-resis		V _{DD} = 3.3 V		1	2	Ω	
rds(on)	V _{BAT} to V _{OUT} on-res	istance	V _{BAT} = 3.3 V		1	2		
		TPS3600x20		1.74	1.78	1.82		
		TPS3600x25		2.17	2.22	2.27		
VIT	Negative-going input	TPS3600x30		2.57	2.63	2.69		
	threshold voltage	TPS3600x33	$T_A = -40^{\circ}C$ to $85^{\circ}C$	2.87	2.93	2.99	V	
	(see Notes 3 and 4)	TPS3600x50		4.31	4.40	4.49		
V _(PFI)	4	PFI		1.13	1.15	1.17		
V(BOK)		TPS3600Dxx		V _{IT} + 5.8%	V _{IT} + 7.1%	V _{IT} + 8.3%		
V(SWN)	Battery switch threshonegative-going VOUT			V _{IT} + 1%	V _{IT} + 2%	V _{IT} + 3.2%	V	

NOTES: 2. The lowest supply voltage at which \overline{RESET} becomes active. $t_{f(VDD)} \ge 15 \,\mu\text{s/V}$.

4. Voltage is sensed at VOUT



^{3.} To ensure best stability of the threshold voltage, a bypass capacitor (ceramic, 0.1 µF) should be placed near the supply terminal.

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electrical characteristics over recommended operating conditions (unless otherwise noted) (continued)

	PARAMETER		TEST CO	ONDITIONS	MIN TY	P MAX	UNIT	
			1.65 V < V _{IT} ·	< 2.5 V	:	20		
		VIT	2.5 V < V _{IT} <	3.5 V		40		
			3.5 V < V _{IT} < 5.5 V		;	50		
			1.65 V < V _(BC)	OK) < 2.5 V	;	30		
		BATTOK	2.5 V < V _{(BO}	K) < 3.5 V	(60		
V_{hys}	Hysteresis		3.5 V < V _{(BO}	K) < 5.5 V	1	00	mV	
		PFI				12		
		V _(BSW)	$V_{DD} = 1.8 \text{ V}$			66		
		V(SWN)	1.65 V < V _{(S\}	_{VN)} < 2.5 V		85		
			2.5 V < V _(SWN) < 3.5 V		1	00		
			3.5 V < V _(SWN) < 5.5 V		1	10		
lін	High-level input current	WDI (see Note 5)	$WDI = V_{DD} = 5 V$			150		
'IH	riigii-ievei iripat carrent	MR	$\overline{MR} = 0.7 \times V_{DD}, V_{DD} = 5 \text{ V}$		-33	-76	μА	
1	Low-level input current	WDI (see Note 5)	WDI = 0 V,	$V_{DD} = 5 V$		-150	μΛ	
lIL.	Low-level input current	MR	$\overline{MR} = 0 \text{ V},$	$V_{DD} = 5 V$	-110	-255		
lį	Input current	PFI, MSWITCH	$V_I < V_{DD}$		-25	25	nA	
			PFO = 0 V,	$V_{DD} = 1.8 \text{ V}$		-0.3		
los	Short-circuit current	PFO	PFO = 0 V,	$V_{DD} = 3.3 \text{ V}$		-1.1	mA	
			$\overline{PFO} = 0 \text{ V},$	$V_{DD} = 5 V$		-2.4		
l	V gupply gurrent		VOUT = VDD			40	^	
IDD	V _{DD} supply current		V _{OUT} = V _{BAT}			8	μΑ	
			V _{OUT} = V _{DD}		-0.1	0.1	^	
I(BAT)	V _{BAT} supply current		V _{OUT} = V _{BAT}			40	μΑ	
l _{lkg}	CEIN leakage current	Disable mode	e, V _I < V _{DD}		±1	μА		
Ci	Input capacitance		$V_{ } = 0 \text{ V to } 5.0$) V		5	pF	

NOTE 5: For details on how to optimize current consumption when using WDI, see the detailed description section.



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timing requirements at R_L = 1 M Ω , C_L = 50 pF, T_A = -40°C to 85°C

PARAMETER TEST CON			TEST CONDITIONS	MIN	TYP	MAX	UNIT
		V_{DD}	$V_{IH} = V_{IT} + 0.2 \text{ V}, V_{IL} = V_{IT} - 0.2 \text{ V}$	5	1		μs
t _w	t _w Pulse width		V V - 00VV 00 - V 07 - V	400			
		WDI	$V_{DD} > V_{IT} + 0.2 \text{ V}, V_{IL} = 0.3 \text{ x } V_{DD}, V_{IH} = 0.7 \text{ x } V_{DD}$	100			ns

switching characteristics at RL= 1 M Ω , CL = 50 pF, TA = -40°C to 85°C

	PARAMI	ETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _d	Delay time		$\frac{V_{DD}}{MR} \ge V_{IT} + 0.2 \text{ V},$ $MR \ge 0.7 \text{ x } V_{DD},$ See timing diagram	60	100	140	ms
t(tout)	Watchdog time-out		V _{DD} > V _{IT} + 0.2 V, See timing diagram	0.48	0.8	1.12	s
tPLH	Propagation (delay) time, low-to-high-level output	50% RESET to 50% CEOUT	V _{OUT} = V _{IT}		15		μs
		V _{DD} to RESET	V _{IL} = V _{IT} - 0.2 V, V _{IH} = V _{IT} + 0.2 V		2	5	μs
		PFI to PFO	$V_{IL} = V_{(PFI)} - 0.2 V,$ $V_{IH} = V_{(PFI)} + 0.2 V$		3	5	μs
^t PHL	Propagation (delay) time, high-to-low-level output	MR to RESET	$V_{DD} \ge V_{IT} + 0.2 \text{ V},$ $V_{IL} = 0.3 \text{ x } V_{DD},$ $V_{IH} = 0.7 \text{ x } V_{DD}$		0.1	1	μs
			V _{DD} = 1.8 V		5	15	ns
		50% CEIN to 50% CEOUT CL = 50 pF only (see Note 6)	V _{DD} = 3.3 V		1.6	5	ns
		OL = 30 pr only (see Note 0)	V _{DD} = 5 V		1	3	ns
	Transition time	V _{DD} to BATTON	$V_{IL} = V_{BAT} - 0.2 \text{ V},$ $V_{IH} = V_{BAT} + 0.2 \text{ V},$ $V_{(BAT)} < V_{IT}$			3	μs

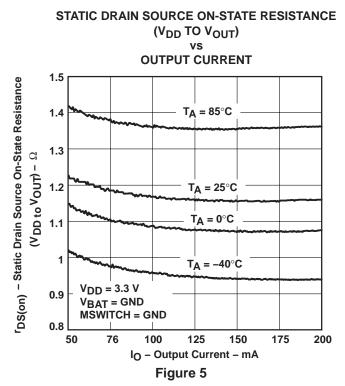
NOTE 6: Ensured by design.

TYPICAL CHARACTERISTICS

Table of Graphs

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` ,	Static Drain-source on-state resistance	vs Chip enable input voltage	7
lDD	Supply current	vs Supply voltage	8, 9
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	Minimum Pulse Duration at V _{DD}	vs Threshold voltage overdrive at V _{DD}	25
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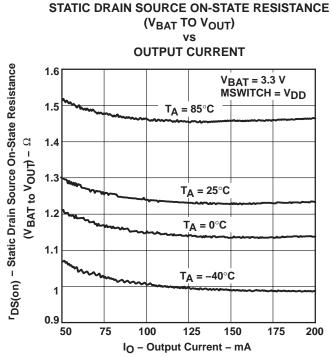
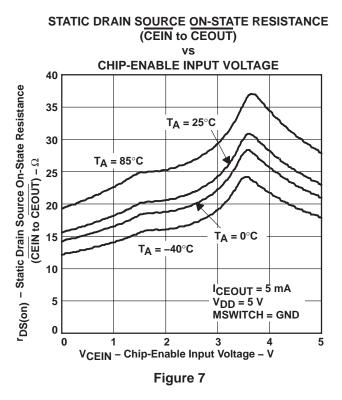
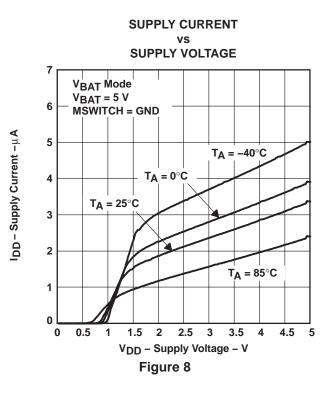
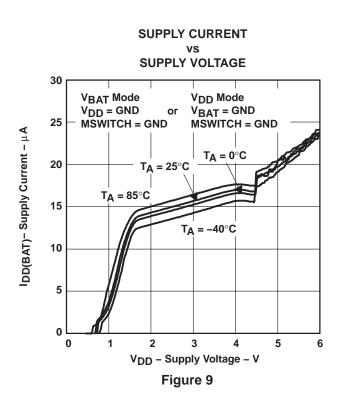
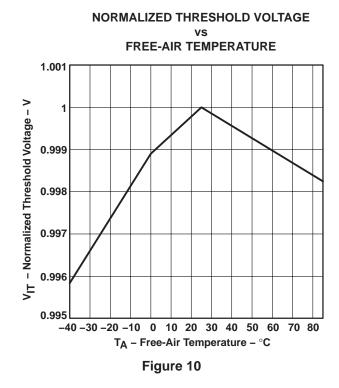


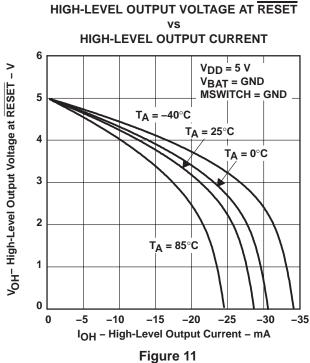
Figure 6

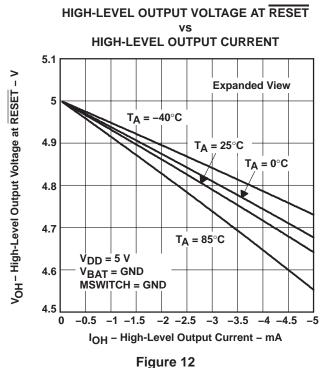












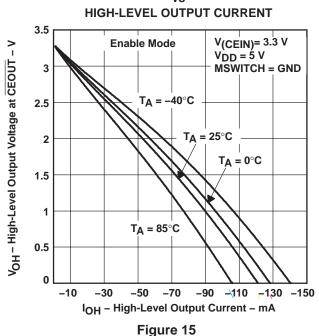
HIGH-LEVEL OUTPUT VOLTAGE AT PFO **HIGH-LEVEL OUTPUT CURRENT** 6 V_{OH} - High-Level Output Voltage at PFO - V 5 $T_A = -40^{\circ}C$ T_A = 25°C 4 $T_A = 0^{\circ}C$ 3 $T_A = 85^{\circ}C$ 2 V_{DD} = 5.5 V 1 PFI = 1.4 V $V_{BAT} = GND$ MSWITCH = GND 0 0 -0.5-1 -1.5-2 -2.5 IOH - High-Level Output Current - mA Figure 13

HIGH-LEVEL OUTPUT CURRENT 5.55 **Expanded View** V_{OH} - High-Level Output Voltage at PFO - V 5.50 $T_A = -40^{\circ}C$ 5.45 T_A = 25°C $T_A = 0^{\circ}C$ 5.40 5.35 5.30 T_A = 85°C 5.25 $V_{DD} = 5.5 V$ 5.20 PFI = 1.4 V V_{BAT} = GND 5.15 MSWITCH = GND 5.10 -20 -40 -60 -80 -100 -120 -140 -160 -180 -200 IOH - High-Level Output Current - µA Figure 14

HIGH-LEVEL OUTPUT VOLTAGE AT PFO

HIGH-LEVEL OUTPUT VOLTAGE AT CEOUT





HIGH-LEVEL OUTPUT VOLTAGE AT CEOUT HIGH-LEVEL OUTPUT CURRENT

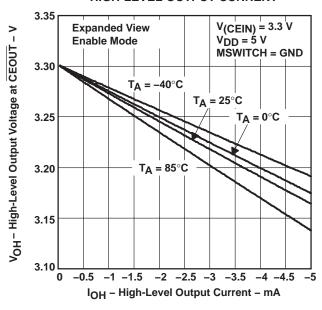
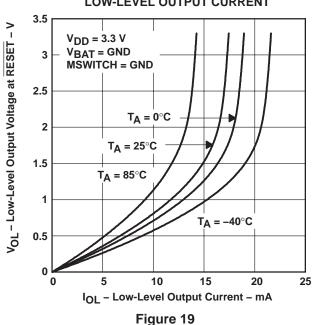


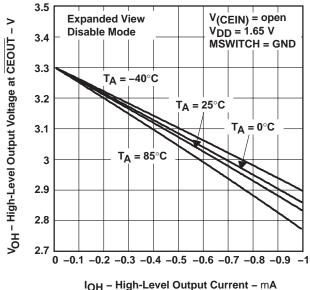
Figure 16

HIGH-LEVEL OUTPUT VOLTAGE AT CEOUT HIGH-LEVEL OUTPUT CURRENT 3.5 VOH - High-Level Output Voltage at CEOUT 3 $T_A = -40^{\circ}C$ T_A = 25°C 2.5 $T_A = 0^{\circ}C$ 2 1.5 T_A = 85°C **Disable Mode** V(CEIN) = open $V_{DD} = 1.65 \text{ V}$ 0.5 MSWITCH = GND 0 -0.5 -1 -1.5 -2 -2.5 0 -3 -3.5-4 -4.5 IOH - High-Level Output Current - mA Figure 17





HIGH-LEVEL OUTPUT VOLTAGE AT CEOUT vs HIGH-LEVEL OUTPUT CURRENT



nigh-Level Output Current - m

Figure 18

LOW-LEVEL OUTPUT VOLTAGE AT RESET vs LOW-LEVEL OUTPUT CURRENT

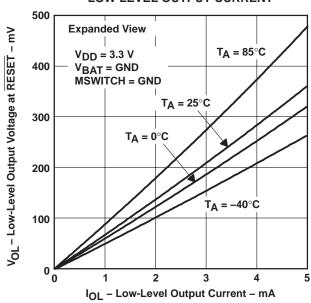


Figure 20



LOW-LEVEL OUTPUT VOLTAGE AT CEOUT vs LOW-LEVEL OUTPUT CURRENT

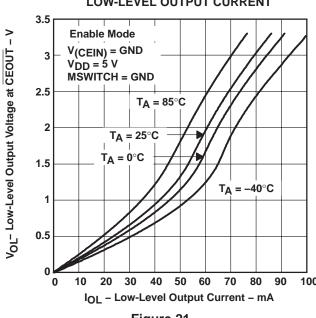


Figure 21

LOW-LEVEL OUTPUT VOLTAGE AT CEOUT vs LOW-LEVEL OUTPUT CURRENT

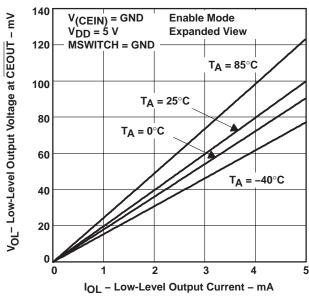


Figure 22

LOW-LEVEL OUTPUT VOLTAGE AT BATTON vs LOW-LEVEL OUTPUT CURRENT

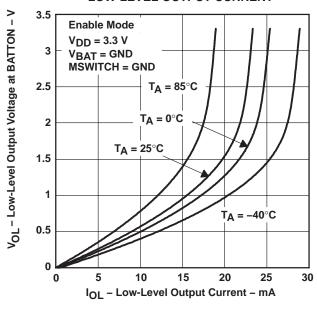
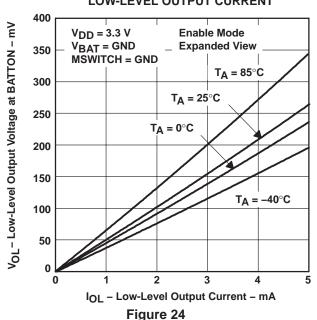


Figure 23

LOW-LEVEL OUTPUT VOLTAGE AT BATTON vs LOW-LEVEL OUTPUT CURRENT



TEXAS INSTRUMENTS www.ti.com

TPS3600D50 MINIMUM PULSE DURATION AT V_{DD} vs THRESHOLD OVERDRIVE AT V_{DD}

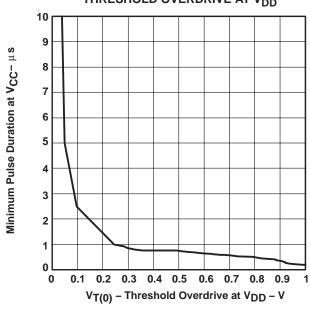


Figure 25

TPS3600D50 MINIMUM PULSE DURATION AT PFI

THRESHOLD OVERDRIVE AT PFI 5 4.6 $V_{DD} = 1.65 V$ Minimum Pulse Duration at PFI – $\mu\,\text{s}$ 4.2 3.8 3.4 3 2.6 2.2 1.8 1.4 1 0.1 0.2 0.3 0.4 0.5 0.6 0.7 0.8 0.9 Threshold Overdrive at PFI - V

Figure 26









PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPS3600D20PW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D20PWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D20PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D20PWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D25PW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D25PWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D25PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D25PWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D33PW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D33PWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D33PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D33PWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D50PW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D50PWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D50PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3600D50PWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



PACKAGE OPTION ADDENDUM

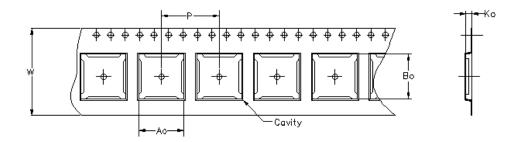
29-Nov-2006

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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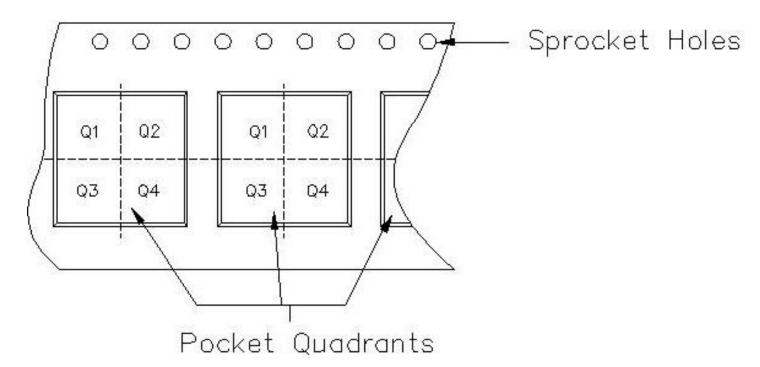
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Carrier tape design is defined largely by the component lentgh, width, and thickness.

Ao =	Dimension	designed	to	accommodate	the	component	width.	
Bo =	Dimension	designed	to	accommodate	the	component	length.	
Ko =	Dímension	designed	to	accommodate	the	component	thickness.	
W = Overall width of the carrier tape.								
P = F	P = Pitch between successive cavity centers.							



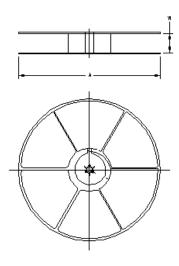
TAPE AND REEL INFORMATION



PACKAGE MATERIALS INFORMATION

21-May-2007

Device	Package	Pins	Site	Reel Diameter (mm)	Reel Width (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS3600D20PWR	PW	14	FRB	0	0	7.0	5.6	1.6	8	12	Q1
TPS3600D25PWR	PW	14	FRB	0	0	7.0	5.6	1.6	8	12	Q1
TPS3600D33PWR	PW	14	FRB	0	0	7.0	5.6	1.6	8	12	Q1
TPS3600D50PWR	PW	14	FRB	0	0	7.0	5.6	1.6	8	12	Q1



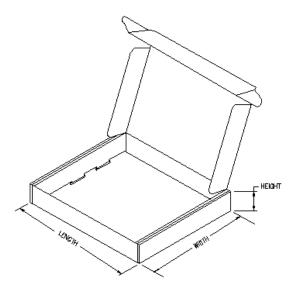
TAPE AND REEL BOX INFORMATION

Device	Package	Pins	Site	Length (mm)	Width (mm)	Height (mm)
TPS3600D20PWR	PW	14	FRB	342.9	336.6	20.6
TPS3600D25PWR	PW	14	FRB	342.9	336.6	20.6
TPS3600D33PWR	PW	14	FRB	342.9	336.6	20.6
TPS3600D50PWR	PW	14	FRB	342.9	336.6	20.6





21-May-2007



PW (R-PDSO-G**)

14 PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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